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☐ Interview Summary (PTO-413), Paper No./Mail Date ☑ Examiner's Amendment/Comm ☑ Examiner's Statement of Reason	nent
	Drawing Review (PTO-948) attached. It / Comment or in the Office action of the written on the drawings in the frecording to 37 CFR 1.121(d). DGICAL MATERIAL must be supposed to the proper of the

DETAILED ACTION

This Office Action is in response to the Election filed December 28, 2004.

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Hosoon Lee on January 14, 2005.

The application has been amended as follows: Please cancel claims 1-8

Election/Restrictions

The Examiner agrees with Applicant's representative that Claim 1 is generic.

Status of Claims

Claims 9-17 are pending. Claims 1-8 are cancelled.

Priority

2. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Allowable Subject Matter

- 3. Claims 9-17 are allowed.
- 4. The following is an examiner's statement of reasons for allowance.
- 6,168,992 to Lee teaches forming interconnects to bit line contact pads but fails to teach forming bit line contact plugs by filling the bit line contact holes with a first

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conductive material, forming damascene bit lines on the bit line contact plugs by filling lower parts of spaces between the oxide layer patterns with the first conductive material, and etching the oxide layer patterns over the bit lines so that only the portions of the oxide layer patterns having the first width protrude above the bit lines; covering the bit lines with a mask layer and planarizing the mask layer until the top surfaces of the oxide layer patterns remaining after step (h) are exposed; selectively removing the remaining oxide layer patterns, the etch stopper under the remaining oxide layer patterns, and the second oxide layer with respect to the mask layer, thereby forming storage node contact holes; and forming storage node contact plugs by filling the storage node contact holes with a second conductive material.

6,337,267 to Yang teaches forming damascene interconnects to a contact pad area but fails to teach forming bit line contact plugs by filling the bit line contact holes with a first conductive material, forming damascene bit lines on the bit line contact plugs by filling lower parts of spaces between the oxide layer patterns with the first conductive material, and etching the oxide layer patterns over the bit lines so that only the portions of the oxide layer patterns having the first width protrude above the bit lines; covering the bit lines with a mask layer and planarizing the mask layer until the top surfaces of the oxide layer patterns remaining after step (h) are exposed; selectively removing the remaining oxide layer patterns, the etch stopper under the remaining oxide layer patterns, and the second oxide layer with respect to the mask layer, thereby forming storage node contact holes; and forming storage node contact plugs by filling the storage node contact holes with a second conductive material.

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6,528,368 to Park teaches forming various width interconnects to cell pads but fails to teach forming bit line contact plugs by filling the bit line contact holes with a first conductive material, forming damascene bit lines on the bit line contact plugs by filling lower parts of spaces between the oxide layer patterns with the first conductive material, and etching the oxide layer patterns over the bit lines so that only the portions of the oxide layer patterns having the first width protrude above the bit lines; covering the bit lines with a mask layer and planarizing the mask layer until the top surfaces of the oxide layer patterns remaining after step (h) are exposed; selectively removing the remaining oxide layer patterns, the etch stopper under the remaining oxide layer patterns, and the second oxide layer with respect to the mask layer, thereby forming storage node contact holes; and forming storage node contact plugs by filling the storage node contact holes with a second conductive material.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David L. Hogans whose telephone number is (571) 272-1691. The examiner can normally be reached on M-F (7:30-4:30).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on (571) 272-1702. The fax phone

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number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

CRAIG A. THOMPSON PRIMARY EXAMINER

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